# onsemi

# **Complementary Silicon Power Transistors**

# D44H Series (NPN), D45H Series (PNP)

These series of plastic, silicon NPN and PNP power transistors can be used as general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

### Features

- Low Collector-Emitter Saturation Voltage
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- These Devices are Pb-Free and are RoHS Compliant\*

### MAXIMUM RATINGS

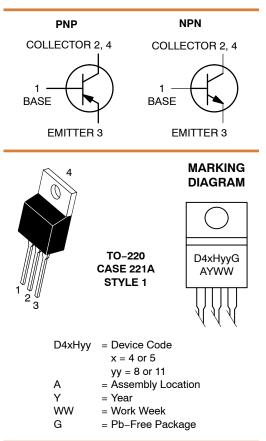
Rating	Symbol	Value	Unit
Collector-Emitter Voltage D44H8, D45H8 D44H11, D45H11	V <sub>CEO</sub>	60 80	Vdc
Emitter Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	10	Adc
Collector Current – Peak (Note 1)	I <sub>CM</sub>	20	Adc
Total Power Dissipation @ $T_C = 25^{\circ}C$ @ $T_A = 25^{\circ}C$	PD	70 2.0	W
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Pulse Width  $\leq$  6.0 ms, Duty Cycle  $\leq$  50%.

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.8	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>0JA</sub>	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	ΤL	275	°C





## **ORDERING INFORMATION**

Device	Package	Shipping
D44H8G	TO-220 (Pb-Free)	50 Units/Rail
D44H11G	TO-220 (Pb-Free)	50 Units/Rail
D45H8G	TO-220 (Pb-Free)	50 Units/Rail
D45H11G	TO–220 (Pb–Free)	50 Units/Rail

\*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

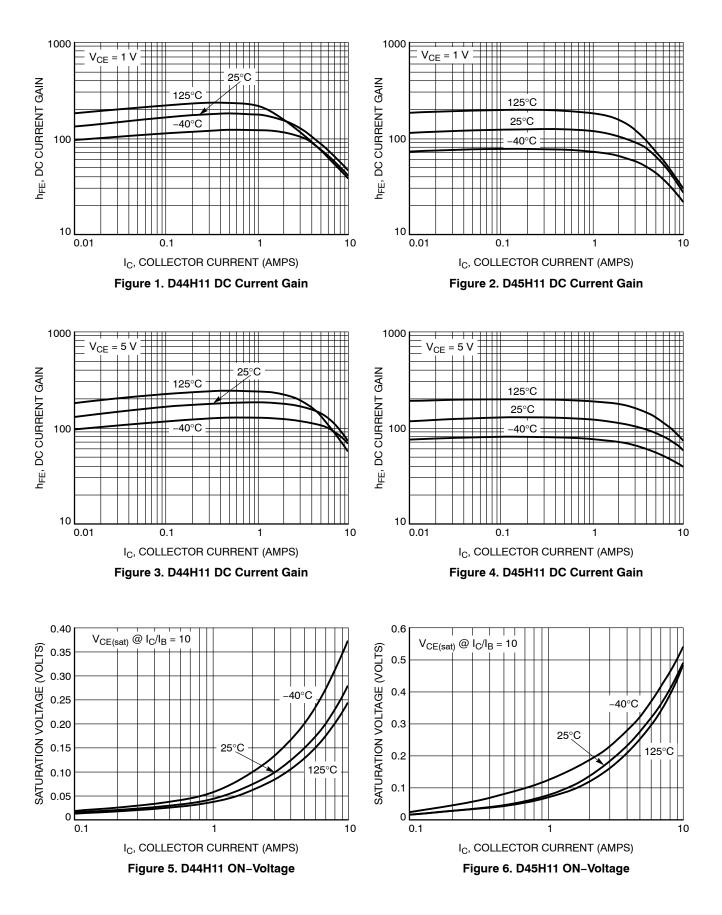
# D44H Series (NPN), D45H Series (PNP)

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						- <u>I</u>
Collector–Emitter Sustaining Voltage ( $I_C = 30 \text{ mAdc}, I_B = 0 \text{ Adc}$ )	D44H8, D45H8 D44H11, D45H11	V <sub>CEO(sus)</sub>	60 80			Vdc
Collector Cutoff Current (V <sub>CE</sub> = Rated V <sub>CEO</sub> , V <sub>BE</sub> =	= 0)	I <sub>CES</sub>	-	-	10	μΑ
Emitter Cutoff Current (V <sub>EB</sub> = 5.0 Vdc)		I <sub>EBO</sub>	_	-	10	μΑ
ON CHARACTERISTICS						
DC Current Gain ( $V_{CE} = 1.0 \text{ Vdc}, I_C = 2.0 \text{ Adc}$ ) ( $V_{CE} = 1.0 \text{ Vdc}, I_C = 4.0 \text{ Adc}$ )		h <sub>FE</sub>	60 40			-
Collector–Emitter Saturation Voltage $(I_C = 8.0 \text{ Adc}, I_B = 0.4 \text{ Adc})$		V <sub>CE(sat)</sub>	_	-	1.0	Vdc
Base-Emitter Saturation Voltage $(I_{\rm C} = 8.0 \text{ Adc}, I_{\rm B} = 0.8 \text{ Adc})$		V <sub>BE(sat)</sub>	_	-	1.5	Vdc
DYNAMIC CHARACTERISTICS						
Collector Capacitance (V <sub>CB</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)	D44H Series D45H Series	C <sub>cb</sub>	-	90 160		pF
Gain Bandwidth Product ( $I_C = 0.5$ Adc, $V_{CE} = 10$ Vdc, f = 20 MHz)	D44H Series D45H Series	fT		50 40		MHz
SWITCHING TIMES						
Delay and Rise Times (I <sub>C</sub> = 5.0 Adc, I <sub>B1</sub> = 0.5 Adc)	D44H Series D45H Series	t <sub>d</sub> + t <sub>r</sub>		300 135		ns
Storage Time (I <sub>C</sub> = 5.0 Adc, I <sub>B1</sub> = I <sub>B2</sub> = 0.5 Adc)	D44H Series D45H Series	t <sub>s</sub>		500 500		ns
Fall Time (I <sub>C</sub> = 5.0 Adc, I <sub>B1</sub> = 102 = 0.5 Adc)	D44H Series D45H Series	t <sub>f</sub>	-	140 100	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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D44H Series (NPN), D45H Series (PNP)

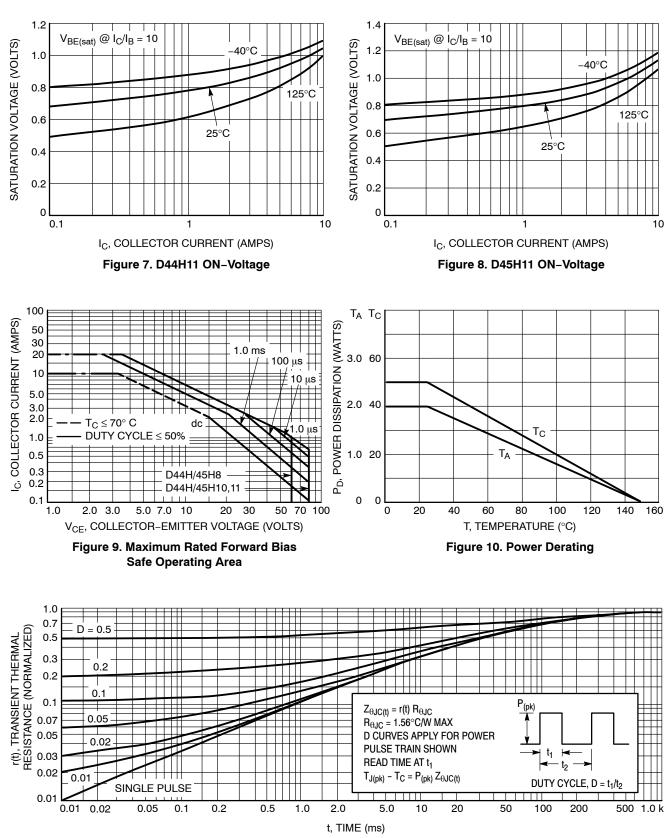


Figure 11. Thermal Response

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SCALE 1:1	TO-22 CASE 22 ISSUE	21A AK SEATING PLANE	DATE 13 JAN NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009. 2. CONTROLLING DIMENSION: INCHES 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED. 4. MAX WIDTH FOR F102 DEVICE = 1.35MM					1, 2009.	
				4. MAX V	WIDTH FOR	F102 DEVICE	= 1.3510101		
	I	Γ I			INC	HES	MILLIM	ETERS	
				DIM	MIN.	MAX.	MIN.	MAX.	
	2 3			А	0.570	0.620	14.48	15.75	
<u> </u>	┟┰┟┟╌┙──┼			В	0.380	0.415	9.66	10.53	
⊢	₩+₩++			С	0.160	0.190	4.07	4.83	
	í lí	f I		D	0.025	0.038	0.64	0.96	
' z –	I I K			F	0.142	0.161	3.60	4.09	
	î î			G	0.095	0.105	2.42	2.66	
				н	0.110	0.161	2.80	4.10	
	¥ ₩	ü l		J	0.014	0.024	0.36	0.61	
V —	R —			ĸ	0.500	0.562	12.70 1.15	14.27	
G	J-	╼║╼		N	0.045	0.060	4.83	1.52 5.33	
Ŭ,	' → → D			Q	0.190	0.210	2.54	3.04	
_	N -			R	0.100	0.120	2.54	2.79	
				s	0.030	0.055	1.15	1.41	
				т	0.235	0.255	5.97	6.47	
				U U	0.000	0.050	0.00	1.27	
				v	0.045		1.15		
				z		0.080		2.04	
2. 3. 4. STYLE 5: PIN 1. 2. 3. 4. STYLE 9: PIN 1. 2. 3.	BASE         PIN 1.           COLLECTOR         2.           EMITTER         3.           COLLECTOR         4.           GATE         PIN 1.           DRAIN         2.           SOURCE         3.           DRAIN         2.           GATE         PIN 1.           CALL         STYLE 10           GATE         PIN 1.           COLLECTOR         2.           EMITTER         3.	BASE EMITTER COLLECTOR EMITTER ANODE CATHODE CATHODE CATHODE	2. 3. 4. STYLE 7: PIN 1. 2. 3. 4. STYLE 11: PIN 1. 2. 3.		E E	2. MA 3. GA 4. MA STYLE 8: PIN 1. CA 2. AN 3. EX 4. AN STYLE 12: PIN 1. MA 2. MA 3. GA	IN TERMINAL THODE DDE TERNAL TRIP DDE IN TERMINAL IN TERMINAL	2 2 /DELAY .2	

 
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